







	<h2 style="color: red;">RFD12N06RLESM9A</h2> <p><b>Hersteller-Teilenummer:</b> <a href="#">RFD12N06RLESM9A</a></p> <p><b>Hersteller / Marke:</b> <a href="#">Fairchild/ON Semiconductor</a></p> <p><b>Teil der Beschreibung:</b> MOSFET N-CH 60V 18A DPAK</p> <p><b>Datenblätter:</b>  <a href="#">RFD12N06RLESM9A.pdf</a></p> <p><b>RoHs Status:</b> Bleifrei / RoHS-konform</p> <p><b>Lagerzustand:</b> New original, 3419 pcs Stock Available.</p> <p><b>Liefern von:</b> Hong Kong</p> <p><b>Versandweg:</b> DHL/Fedex/TNT/UPS/EMS</p>
	
<p>Image may be representation. See specs for product details.</p>	

### Spezifikationen

Teilenummer	<a href="#">RFD12N06RLESM9A</a>
Hersteller	<a href="#">Fairchild/ON Semiconductor</a>
Beschreibung	MOSFET N-CH 60V 18A DPAK
Kategorie	<a href="#">Diskrete Halbleiterprodukte &gt; Transistoren-FETs,</a>
Teilstatus	3419 pcs Stock
Serie	UltraFET™
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 175°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-252-3, DPak (2 Leads + Tab), SC-63
Supplier Device-Gehäuse	TO-252AA
Verlustleistung (max)	49W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	60V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	18A (Tc)
Rds On (Max) @ Id, Vgs	63 mOhm @ 18A, 10V
VGS (th) (Max) @ Id	3V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	15nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	485pF @ 25V
Antriebsspannung (Max Rds On, Min Rds On)	4.5V, 10V
Vgs (Max)	±16V
Verpackung	Tape & Reel (TR)

RFD12N06RLESM9A ist neu im Original, Suche RFD12N06RLESM9A Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie RFD12N06RLESM9A Fairchild/ON Semiconductor mit Garantie und Vertrauen. Anfrage RFD12N06RLESM9A: [Info@Y-IC.com](mailto:Info@Y-IC.com)

Sie können auch interessiert sein:

 <b>RFD12N06RLESM F</b> F RFD12N06RLESM F	 <b>RFD12N06RLESM9A</b> AMI Semiconductor / ON Semiconductor MOSFET N-CH 60V 18A DPAK	 <b>RFD14N05</b> AMI Semiconductor / ON Semiconductor MOSFET N-CH 50V 14A I-PAK	 <b>RFD12N06RLE</b> AMI Semiconductor / ON Semiconductor MOSFET N-CH 60V 18A IPAK
 <b>RFD12N06REL F</b> F RFD12N06REL F	 <b>RFD14N05L</b> AMI Semiconductor / ON Semiconductor MOSFET N-CH 50V 14A I-PAK	 <b>RFD12N06LESM F</b> F RFD12N06LESM F	 <b>RFD12N06RLE</b> Fairchild/ON Semiconductor MOSFET N-CH 60V 18A IPAK

### heiße Teile

Mehr

RFD10N05SM96	RFD10P03L-251	RFD10P03LSM	RFD10P03LSM	RFD10P05
RFD12N06LE	RFD12N06LESM	RFD12N06REL	RFD12N06RLE	RFD12N06RLE
RFD12N06RLESM	RFD12N06RLESM9A	RFD14N05	RFD14N05	RFD14N05L
RFD14N05L	RFD14N05LSM	RFD14N05LSM	RFD14N05LSM9A	RFD14N05LSM9A
RFD14N05SM	RFD14N05SM	RFD14N05SM9	RFD14N05SM9A	RFD14N05SM9A
RFD15N05	RFD15N05LSM	RFD15N06LE	RFD15N06LESM	RFD15P05
RFD15P05	RFD15P05SM	RFD15P05SM	RFD15P05SM9A	RFD15P06
RFD15P06LSM	RFD15P06SM	RFD15P06SM9AS2463	RFD16N02	RFD16N02L
RFD16N02LSM	RFD16N02LSM9A	RFD16N03L	RFD16N03LSM	RFD16N03LSM9A
RFD16N05	RFD16N05	RFD16N05L	RFD16N05LSM	RFD16N05LSM

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